

ABSTRACT

PRECURSOR COMPOSITION FOR FORMING METAL FILM, METAL FILM
FORMING METHOD USING SAME, AND SEMICONDUCTOR DEVICE
5 COMPRISING SAME METAL FILM

Proposed is a precursor composition for forming a metal
film including a zirconium compound represented by any one
of Chemical Formulas 1 to 3 and a hafnium compound
10 represented by any one of Chemical Formulas 4 to 6.

(FIG. 1)